

NTE2507 Silicon NPN Transistor High Frequency Video Output

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector–Base Voltage, V_{CBO}	200V
Collector–Emitter Voltage, V_{CEO}	200V
Emitter–Base Voltage, V_{EBO}	5V
Collector Current, I_C	400mA
Collector Power Dissipation ($T_C = +25^\circ\text{C}$), P_C	20W
Operating Junction Temperature, T_J	+150°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 150\text{V}$	–	–	0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = 10\text{V}$, $I_C = 50\text{mA}$	40	–	320	
Transition Frequency	f_T	$V_{CE} = 30\text{V}$, $I_C = 100\text{mA}$	–	400	–	MHz
Output Capacitance	C_{ob}		–	4.2	–	pF

